

SEMICONDUCTOR TECHNICAL DATA

KTD2058

TRIPLE DIFFUSED NPN TRANSISTOR

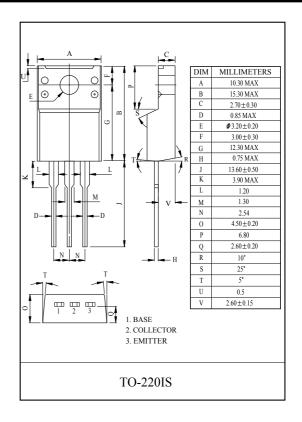
GENERAL PURPOSE APPLICATION.

FEATURES

- · Low Saturation Voltage
 - : $V_{CE(sat)}=1.0V(Max.)$ at $I_{C}=2A$, $I_{B}=0.2A$.
- · Complementary to KTB1366.

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT				
Collector-Base Voltage		V_{CBO}	60	V				
Collector-Emitter Voltage		V _{CEO}	60	V				
Emitter-Base Voltage		V _{EBO}	7	V				
Collector Current		I_{C}	3	A				
Base Current		I_{B}	0.5	A				
Collector Power	Ta=25 ℃	P_{C}	2	W				
Dissipation	Tc=25 ℃	10	25					
Junction Temperature		T _j	150	${\mathbb C}$				
Storage Temperature Range		T_{stg}	-55 ~ 150	${\mathbb C}$				

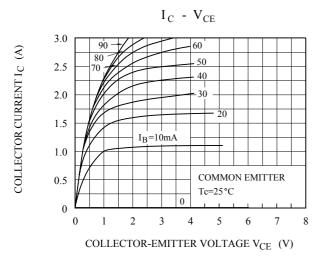


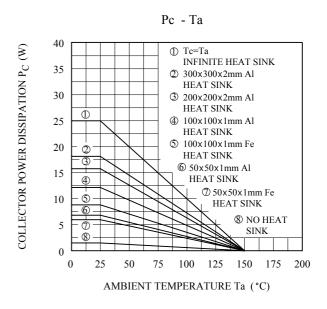
ELECTRICAL CHARACTERISTICS (Ta=25°C)

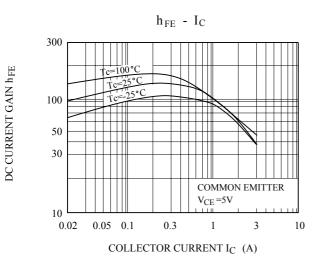
CHARAC	TERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Cu	irrent	I_{CBO}	$V_{CB} = 60V, I_{E} = 0$	-	-	100	μA
Emitter Cut-off Curi	rent	I_{EBO}	$V_{EB}=7V$, $I_{C}=0$	-	-	100	μ A
Collector-Emitter Br	reakdown Voltage	V _{(BR)CEO}	$I_{C}=50 \text{mA}, I_{B}=0$	60	-	-	V
DC Current Gain		h _{FE} (Note)	$V_{CE} = 5V, I_{C} = 0.5A$	60	-	200	
Collector Emitter Sa	turation Voltage	V _{CE(sat)}	I _C =2A, I _B =0.2A	-	0.25	1.0	V
Base-Emitter Voltag	ge	V_{BE}	$V_{CE} = 5V, I_{C} = 0.5A$	-	0.7	1.0	V
Transition Frequenc	y	f_T	$V_{CE} = 5V, I_{C} = 0.5A$	-	3.0	-	MHz
Collector Output Capacitance		C _{ob}	$V_{CB}=10V, I_{E}=0, f=1MHz$	-	35	-	pF
Switching	Turn-on Time	t _{on}	$I_{B1} = I_{B2} = 0.2A$ DUTY CYCLE $\leq 1\%$ OUTPUT $I_{B1} = I_{B2} = 0.2A$ $V_{CC} = 30V$	-	0.65	-	
	Storage Time	t _{stg}		-	1.3	-	μS
	Fall Time	${ m t_f}$		-	0.65	-	

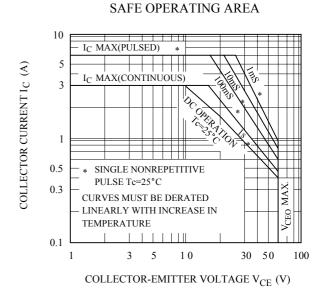
Note: h_{FE} Classification O:60~120, Y:100~200

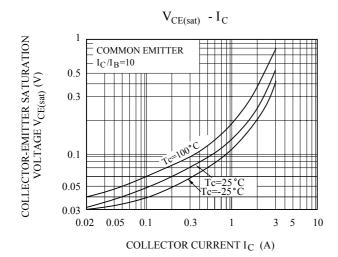
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This datasheet has been download from:

 $\underline{www.datasheet catalog.com}$

Datasheets for electronics components.